



PTO/SB/21 (08-00)

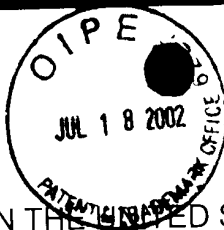
<b>TRANSMITTAL FORM</b>  (to be used for all correspondence after initial filing)	Application Number	09/412,512
	Filing Date	October 5, 1999
	First Named Inventor	Shunpei YAMAZAKI
	Group Art Unit	2812
	Examiner Name	R. Booth
	Attorney Docket Number	0756-2046
Total Number of Pages in This Submission		

ENCLOSURES (check all that apply)		
<input type="checkbox"/> Fee Transmittal Form <input checked="" type="checkbox"/> Fee Attached <input type="checkbox"/> Amendment / Reply <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input checked="" type="checkbox"/> Extension of Time Request <input type="checkbox"/> Express Abandonment Request <input checked="" type="checkbox"/> Notification of Related Applications <input type="checkbox"/> Certified Copy of Priority Document(s) <input type="checkbox"/> Response to Missing Parts/Incomplete Application <input type="checkbox"/> Response to Missing Parts under 37 CFR 1.52 or 1.53	<input type="checkbox"/> Assignment Papers (for an Application) <input type="checkbox"/> Drawing(s) <input type="checkbox"/> Declaration and Power of Attorney <input type="checkbox"/> Licensing-related Papers <input type="checkbox"/> Petition <input type="checkbox"/> Petition to Convert to a Provisional Application <input type="checkbox"/> Power of Attorney, Revocation Change of Correspondence Address <input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Request for Refund <input type="checkbox"/> CD, Number of CD(s)	<input type="checkbox"/> After Allowance Communication to Group <input type="checkbox"/> Appeal Communication to Board of Appeals and Interferences <input type="checkbox"/> Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) <input type="checkbox"/> Proprietary Information <input type="checkbox"/> Status Letter <input checked="" type="checkbox"/> Other Enclosures 1. Change of Correspondence Address Form 2. 3. 4. 5. 6.
Remarks		<input checked="" type="checkbox"/> The Commissioner is hereby authorized to charge any additional fees required or credit any overpayments to Deposit Account No. 50-2280 for the above identified docket number.

SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT		FEE VALUE ACCOUNTABILITY
Firm or Individual name	Eric J. Robinson, Reg. No. 38,285 Robinson Intellectual Property Law Office, P.C. PMB 955 21010 Southbank Street Potomac Falls, VA 20165	DEPOSIT ACCOUNT NO.
Signature		FEE CODE
Date	July 15, 2002	VALUE FORWARDED

CERTIFICATE OF MAILING			
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- 1 -

Docket: 0756-2046

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of ) Art Unit: 2812  
Shunpei YAMAZAKI ) Examiner: R. Booth  
Serial No. 09/412,512 )  
Filed: October 5, 1999 )  
For: LIQUID CRYSTAL DISPLAY )  
DEVICE, ACTIVE MATRIX TYPE )  
LIQUID CRYSTAL DISPLAY )  
DEVICE, AND METHOD OF )  
DRIVING THE SAME )

**CERTIFICATE OF MAILING**

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**NOTIFICATION OF RELATED APPLICATIONS**

Honorable Commissioner of Patents  
Washington, D.C. 20231

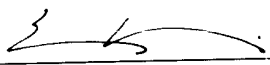
Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith an attached Form PTO-1449 listing related applications known to Applicant and requests that this information be made of record in the above identified application. Copies of the related applications are submitted herewith in accordance with 37 C.F.R. 1.98(a).

A check in the amount of \$180 is being submitted to comply with the provisions of 37 C.F.R. § 1.97(c).

The Commissioner is hereby authorized to charge any fees connected with this filing which may be required now, or credit any overpayment to Deposit Account No. 50-2280.

Respectfully submitted,

  
Eric J. Robinson  
Reg. No. 38,285

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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/894,125	06/29/2001	Shunpei Yamazaki	740756-2330	7248

22204 7590 04/24/2002

NIXON PEABODY, LLP  
8180 GREENSBORO DRIVE  
SUITE 800  
MCLEAN, VA 22102



EXAMINER

KEBEDE, BROOK

ART UNIT PAPER NUMBER

2823

DATE MAILED: 04/24/2002

Please find below and/or attached an Office communication concerning this application or proceeding.

04/29/02 DOCKETED By CNB  
Nixon Peabody, LLP

## Office Action Summary



Application No.

09/894,125

Applicant(s)

YAMAZAKI ET AL.

Examiner

Brook Kebede

Art Unit

2823

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

## Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

## Status

- 1) ☐ Responsive to communication(s) filed on 29 June 2001.
- 2a) ☐ This action is FINAL. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

## Disposition of Claims

- 4) ☐ Claim(s) 1-46 is/are pending in the application.
- 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☐ Claim(s) 1-46 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

## Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on \_\_\_\_\_ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

## Priority under 35 U.S.C. §§ 119 and 120

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some \* c) ☐ None of:
- ☐ Certified copies of the priority documents have been received.
  - ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
  - ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- \* See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

## Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) \_\_\_\_\_
- 4) ☐ Interview Summary (PTO-413) Paper No(s) \_\_\_\_\_
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: \_\_\_\_\_



## DETAILED ACTION

### *Response to Amendment*

1. The preliminary amendment filed on December 19, 2001 is objected to under 35 U.S.C. 132 because it introduces new matter into the disclosure. 35 U.S.C. 132 states that no amendment shall introduce new matter into the disclosure of the invention. The added material which is not supported by the original disclosure is as follows:

Although the specification has support for EL (electro-luminescence) display device as originally filled, it has no support for organic EL (electro-luminescence) display as amended in Page 16, Paragraph 6, through Page 17. The newly added term "organic" doesn't have support in the disclosure as originally filled.

Similarly the newly added claims, i.e. claims 33-46, have no support in the specification for the term "organic" as the disclosure filled originally. Applicants are required to cancel the new matter in the reply to this Office Action.

### *Information Disclosure Statement*

2. The information disclosure statement filed on June 29, 2001 in Paper No. 2 fails to comply with 37 CFR 1.98(a)(2), which requires a legible copy of each U.S. and foreign patent; each publication or that portion which caused it to be listed; and all other information or that portion which caused it to be listed. It has been placed in the application file, but the information referred to therein has not been considered.

### *Claim Objections*

3. Claims 21-30 are objected to because of the following informalities:

Claims 31-30 recite the limitation "A method manufacturing a semiconductor device according to any one of claim ...". Since each of claims 21-30 depend on a single claim, i.e., claim 19 or 20, the preamble seems typo. As suggestion change "A method

manufacturing a semiconductor device according to any one of claim" to -- A method manufacturing a semiconductor device according to claim-- Appropriate correction is required.

***Claim Rejections - 35 USC § 112***

4. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

5. Claims 33-46 are rejected under 35 U.S.C. 112, first paragraph, as containing subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention.

Claims 33-46 the limitation "organic EL electro-luminescence display device" in line 2. However, the term "organic" has no support in the specification as the disclosure originally filled. Therefore, the claimed subject matter was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention.

6. The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

7. Claims 1-6, 18, 19, 31 and 32-46 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Claims 1-6 and 19 are recite the limitation "removing an oxide film from a surface of the semiconductor film by etching after the irradiation of the laser light" in

lines 5-6, for claims 1-6, and lines 6-7, for claim 19 respectively. Since there is no mention of formation an oxide film before the removing step, the claim lacks antecedent basis.

Claim 18, as being dependent of any one of base independent claims 1-12, recites "wherein said semiconductor device is at least one selected form the group consisting of a personal computer, a video camera, a mobile computer, a player using a recording medium, a goggle-type display, a digital camera, and a projector" Since all the base independent claims are clearly call for process of forming the device which is a thin crystalline silicon film transistor (TFT), the claim does not establish a base how different embodiments of a personal computer or a video camera or a mobile computer or a player using a recording medium or a goggle-type display or a digital camera or a projector are formed. Therefore, the scope of the claim cannot be determined and the claim is vague and indefinite. Also see *Ex parte Lyell* 17 USPQ2d 1548 (8/16/1990).

Claim 31, as being dependent of base independent claim 19, recites "wherein said semiconductor device is at least one selected form the group consisting of a personal computer, a video camera, a mobile computer, a player using a recording medium, a goggle-type display, a digital camera, and a projector" Since the base independent claim is clearly call for process of forming the device which is a thin crystalline silicon film transistor (TFT), the claim does not establish a base how different embodiments of a personal computer or a video camera or a mobile computer or a player using a recording medium or a goggle-type display or a digital camera or a projector are formed. Therefore, the scope of the claim cannot be determined and the claim is vague and indefinite. Also see *Ex parte Lyell* 17 USPQ2d 1548 (8/16/1990).

Claim 32, as being dependent of base independent claim 20, recites "wherein said semiconductor device is at least one selected from the group consisting of a personal computer, a video camera, a mobile computer, a player using a recording medium, a goggle-type display, a digital camera, and a projector" Since the base independent claim is clearly call for process of forming the device which is a thin crystalline silicon film transistor (TFT), the claim does not establish a base how different embodiments of a personal computer or a video camera or a mobile computer or a player using a recording medium or a goggle-type display or a digital camera or a projector are formed. Therefore, the scope of the claim cannot be determined and the claim is vague and indefinite. Also see *Ex parte Lyell* 17 USPQ2d 1548 (8/16/1990).

Claims 33-45, as being dependent of base independent claims 1-12, 19, and 20 respectively, recite "wherein said semiconductor device is an organic electro-luminescence display device." Since the base independent claims are clearly call for process of forming the device which is a thin crystalline silicon film transistor (TFT), the claims do not establish a base how different embodiments of an organic electro-luminescence display device are formed. Therefore, the scope of the claim cannot be determined and the claim is vague and indefinite. Also see *Ex parte Lyell* 17 USPQ2d 1548 (8/16/1990).

Accordingly, claims 18, 31-46 have not been further treated on the merit.

### ***Claim Rejections - 35 USC § 102***

8. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.



9. Claims 1-17 and 19-30 rejected under 35 U.S.C. 102(e) as being anticipated by Yamazaki et al. (US/6,077,731).

Re claims 1-12, 19 and 20, Yamazaki et al. disclose a method of manufacturing a semiconductor device comprising the steps of: forming a semiconductor film comprising silicon over a substrate; irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film; removing an oxide film from a surface of the semiconductor film by etching after the irradiation of the laser light; and leveling the surface of the semiconductor film by heating after removing said oxide film (see Figs. 5A - 6F) by containing the concentration of oxygen or oxide compound less than 1 ppm (i.e. less than 10 ppm as claimed) (see Col. 13, lines 10-18); and leveling the surface of the semiconductor film by heating after the treatment with said hydrofluoric acid in reducing atmosphere such as hydrogen or inert gases such as nitrogen (see Col. 1, line 5 - Col. 128, line 65).

Re claim 13, as applied to claims 1-12 above, Yamazaki et al. disclose all the claimed limitations including the limitation wherein the step of leveling the surface of said semiconductor film is conducted by furnace annealing (see Col. 1, line 5 - Col. 128, line 65).

Re claim 14, as applied to claims 1-12 above, Yamazaki et al. disclose all the claimed limitations including the limitation wherein the step of leveling the surface of said semiconductor film is conducted between 900 and 1200° C see Col. 1, line 5 - Col. 128, line 65).

Re claim 15, as applied to claims 3, 6, 9, and 12 above, Yamazaki et al. disclose all the claimed limitations including the limitation wherein said inert gas is nitrogen.

Re claim 16, as applied to claims 2, 5, 8, and 11 above, Yamazaki et al. disclose all the claimed limitations including the limitation wherein said reducing atmosphere comprises hydrogen see Col. 1, line 5 – Col. 128, line 65).

Re claim 17, as applied to claims 1-12 above, Yamazaki et al. disclose all the claimed limitations including the step of treating a surface of the semiconductor film with a buffered hydrofluoric acid before the irradiation of the laser light see Col. 1, line 5 – Col. 128, line 65).

Re claim 21, as applied to claim 19 above, Yamazaki et al. disclose all the claimed limitations including wherein the step of leveling the surface of said semiconductor film is conducted by furnace annealing see Col. 1, line 5 – Col. 128, line 65).

Re claim 22, as applied to claim 20 above, Yamazaki et al. disclose all the claimed limitations including wherein the step of leveling the surface of said semiconductor film is conducted by furnace annealing see Col. 1, line 5 – Col. 128, line 65).

Re claim 23, as applied to claim 19 above, Yamazaki et al. disclose all the claimed limitations including wherein the step of leveling the surface of said semiconductor film is conducted between 900 and 1200° C see Col. 1, line 5 – Col. 128, line 65).

Re claim 24, as applied to claim 20 above, Yamazaki et al. disclose all the claimed limitations including wherein the step of leveling the surface of said semiconductor film is conducted between 900 and 1200° C see Col. 1, line 5 – Col. 128, line 65).

Re claim 25, as applied to claim 19 above, Yamazaki et al. disclose all the claimed limitations including wherein said atmosphere in said leveling step contains an inert gas see Col. 1, line 5 – Col. 128, line 65).

Re claim 26, as applied to claim 20 above, Yamazaki et al. disclose all the claimed limitations including wherein said atmosphere in said leveling step contains an inert gas see Col. 1, line 5 – Col. 128, line 65).

Re claim 27, as applied to claim 19 above, Yamazaki et al. disclose all the claimed limitations including wherein said atmosphere in said leveling step contains a reducing atmosphere see Col. 1, line 5 – Col. 128, line 65).

Re claim 28, as applied to claim 20 above, Yamazaki et al. disclose all the claimed limitations including wherein said atmosphere in said leveling step contains a reducing atmosphere see Col. 1, line 5 – Col. 128, line 65).

Re claim 29, as applied to claim 19 above, Yamazaki et al. disclose all the claimed limitations including further comprising a step of treating a surface of the semiconductor film with a buffered hydrofluoric acid before the irradiation of the laser light see Col. 1, line 5 – Col. 128, line 65).

Re claim 30, as applied to claim 20 above, Yamazaki et al. disclose all the claimed limitations including a step of treating a surface of the semiconductor film with a buffered hydrofluoric acid before the irradiation of the laser light see Col. 1, line 5 – Col. 128, line 65).

### ***Conclusion***

10. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure Zhang et al. (US/5,481,121), Yamazaki (US/5,514,879), Zhang et al. (US5,578,520), Zhang et al. (US/5,604,360), Ohtani et al. (US/5,605,846), Teramoto

(US/5,620,910), Kousai et al. (US/5,795,795), Yamazaki et al. (US/5,693,541). Mitanaga et al. (US/5,808,321) also disclose similar inventive subject matter including laser annealing process of the amorphous silicon in air.

*Correspondence*

11. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Brook Kebede whose telephone number is (703) 306-4511. The examiner can normally be reached on 8-5 Monday to Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (703) 308-4918. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7722 for regular communications and (703) 308-7722 for After Final communications.

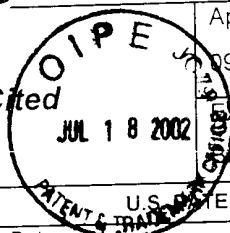
Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Brook Kebede

*BK*  
April 21, 2002

*L. Ph*  
LONG PHAM  
PRIMARY EXAMINER

# Notice of References Cited



Application/Control No.

09/894,125

Applicant(s)/Patent Under Reexamination  
YAMAZAKI ET AL.

Examiner

Brook Kebede

Art Unit

2823

Page 1 of 1

## U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-5,481,121	01-1996	Zhang et al.	257/291
	B	US-5,514,879	05-1996	Yamazaki, Shunpei	257/65
	C	US-5,578,520	11-1996	Zhang et al.	117/200
	D	US-5,604,360	02-1997	Zhang et al.	257/347
	E	US-5,605,846	02-1997	Ohtani et al.	148/DIG.16
	F	US-5,620,910	04-1997	Teramoto, Satoshi	438/151
	G	US-5,795,795	08-1998	Kousai et al.	117/106
	H	US-5,693,541	12-1997	Yamazaki et al.	148/DIG.16
	I	US-5,808,321	09-1998	Mitanaga et al.	257/351
	J	US-6,077,731	06-2000	Yamazaki et al.	438/150
	K	US-			
	L	US-			
	M	US-			

## FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

## NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	
	V	
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

JUL 18 2002



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WASHINGTON, D.C. 20231  
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APPLICATION NUMBER	FILING DATE	GRP ART UNIT	FIL FEE REC'D	ATTY DOCKET NO	DRAWINGS	TOT CLAIMS	IND CLAIMS
09/894,125	06/29/2001	2823	3074	740756-2330	9	18	12

CONFIRMATION NO. 7248

22204  
NIXON PEABODY, LLP  
8180 GREENSBORO DRIVE  
SUITE 800  
MCLEAN, VA 22102

## FILING RECEIPT



\*OC00000006351043\*

Date Mailed: 07/27/2001

Receipt is acknowledged of this nonprovisional Patent Application. It will be considered in its order and you will be notified as to the results of the examination. Be sure to provide the U.S. APPLICATION NUMBER, FILING DATE, NAME OF APPLICANT, and TITLE OF INVENTION when inquiring about this application. Fees transmitted by check or draft are subject to collection. Please verify the accuracy of the data presented on this receipt. If an error is noted on this Filing Receipt, please write to the Office of Initial Patent Examination's Customer Service Center. Please provide a copy of this Filing Receipt with the changes noted thereon. If you received a "Notice to File Missing Parts" for this application, please submit any corrections to this Filing Receipt with your reply to the Notice. When the USPTO processes the reply to the Notice, the USPTO will generate another Filing Receipt incorporating the requested corrections (if appropriate).

## Applicant(s)

Shunpei Yamazaki, Atsugi-shi, JAPAN;  
Hisashi Ohtani, Atsugi-shi, JAPAN;  
Tamae Takano, Atsugi-shi, JAPAN;

## Domestic Priority data as claimed by applicant

THIS APPLICATION IS A DIV OF 09/352,198 07/13/1999

## Foreign Applications

JAPAN 10-203205 07/17/1998  
JAPAN 11-135055 05/14/1999

If Required, Foreign Filing License Granted 07/26/2001

Projected Publication Date: 11/01/2001

Non-Publication Request: No

Early Publication Request: No

## Title

Crystalline semiconductor thin film, method of fabricating the same, semiconductor device and method of fabricating the same

Handwritten signature and date: 07/27/01



1. A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon over a substrate;  
irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film;

removing an oxide film from a surface of the semiconductor film by etching after the irradiation of the laser light; and

leveling the surface of the semiconductor film by heating after removing said oxide film.

2. A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon over a substrate;  
irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film;

removing an oxide film from a surface of the semiconductor film by etching after the irradiation of the laser light; and

leveling the surface of the semiconductor film by heating in a reducing atmosphere after removing said oxide film.

3. A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon over a substrate;  
irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film;

removing an oxide film from a surface of the semiconductor film by etching after the irradiation of the laser light; and

leveling the surface of the semiconductor film by heating in an inert gas after removing said oxide film.

4. A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon over a substrate;  
irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film;

removing an oxide film from a surface of the semiconductor film by etching after the irradiation of the laser light; and

leveling the surface of the semiconductor film by heating in an atmosphere after removing said oxide film, a concentration of oxygen or a oxygen compound contained in said atmosphere is 10 ppm or less.

5. A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon over a substrate;  
irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film;

removing an oxide film from a surface of the semiconductor film by etching after the irradiation of the laser light; and

leveling the surface of the semiconductor film by heating in a reducing atmosphere after removing said oxide film, a concentration of oxygen or a oxygen compound contained in said reducing atmosphere is 10 ppm or less.

6. A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon over a substrate;  
irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film;



removing an oxide film from a surface of the semiconductor film by etching after the irradiation of the laser light; and

leveling the surface of the semiconductor film by heating in an inert gas after removing said oxide film, a concentration of oxygen or a oxygen compound contained in said inert gas is 10 ppm or less.

7. A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon over a substrate;

irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film;

treating a surface of the semiconductor film with a hydrofluoric acid after the irradiation of the laser light; and

leveling the surface of the semiconductor film by heating after the treatment with said hydrofluoric acid.

8. A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon over a substrate;

irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film;

treating a surface of the semiconductor film with a hydrofluoric acid after the irradiation of the laser light; and

leveling the surface of the semiconductor film by heating after the treatment with said hydrofluoric acid in a reducing atmosphere.

9. A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon over a substrate;

irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film;

treating a surface of the semiconductor film with a hydrofluoric acid after the irradiation of the laser light; and

leveling the surface of the semiconductor film by heating after the treatment with said hydrofluoric acid in an inert gas.

10. A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon over a substrate;

irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film;

treating a surface of the semiconductor film with a hydrofluoric acid after the irradiation of the laser light; and

leveling the surface of the semiconductor film by heating after the treatment with said hydrofluoric acid in an atmosphere, a concentration of oxygen or a oxygen compound contained in said atmosphere is 10 ppm or less.

11. A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon over a substrate;

irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film;

treating a surface of the semiconductor film with a hydrofluoric acid after the irradiation of the laser light; and

leveling the surface of the semiconductor film by heating after the treatment with said hydrofluoric acid in a reducing atmosphere, a concentration of oxygen or a oxygen compound contained in said reducing atmosphere is 10 ppm or less.

12. A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon over a substrate;  
irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film;

treating a surface of the semiconductor film with a hydrofluoric acid after the irradiation of the laser light; and

leveling the surface of the semiconductor film by heating after the treatment with said hydrofluoric acid in an inert gas, a concentration of oxygen or a oxygen compound contained in said inert gas is 10 ppm or less.

13. A method of manufacturing a semiconductor device according to any one of claims 1-12, wherein the step of leveling the surface of said semiconductor film is conducted by furnace annealing.

14. A method of manufacturing a semiconductor device according to any one of claims 1-12, wherein the step of leveling the surface of said semiconductor film is conducted between 900 and 1200° C.

15. A method of manufacturing a semiconductor device according to any one of claims 3, 6, 9, and 12, wherein said inert gas is nitrogen.

16. A method of manufacturing a semiconductor device according to any one of claims 2, 5, 8, and 11, wherein said reducing atmosphere comprises hydrogen.

17. A method of manufacturing a semiconductor device according to any one of claims 1-12, further comprising a step of treating a surface of the semiconductor film with a buffered hydrofluoric acid before the irradiation of the laser light.

18. A method of manufacturing a semiconductor device according to any one of claims 1-12, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a mobile computer, a player using a recording medium, a goggle-type display, a digital camera, and a projector.

19. A method of manufacturing a semiconductor device comprising the steps of:  
forming a semiconductor film comprising silicon over a substrate;  
irradiating said semiconductor film with a laser light in an atmosphere containing oxygen for crystallizing said semiconductor film;  
removing an oxide film from a surface of the semiconductor film by etching after the irradiation of the laser light; and  
leveling the surface of the semiconductor film by heating in an atmosphere after removing said oxide film, a concentration of oxygen or a oxygen compound contained in said atmosphere is 10 ppm or less.

20. A method of manufacturing a semiconductor device comprising the steps of:  
forming a semiconductor film comprising silicon over a substrata;  
irradiating said semiconductor film with a laser light in an atmosphere contained oxygen for crystallizing said semiconductor film;  
treating a surface of the semiconductor film with a hydrofluoric acid after the irradiation of the laser light; and

leveling the surface of the semiconductor film by heating after the treatment with said hydrofluoric acid in an atmosphere, a concentration of oxygen or a oxygen compound contained in said atmosphere is 10 ppm or less.

21. A method of manufacturing a semiconductor device according to any one of claim 19, wherein the step of leveling the surface of said semiconductor film is conductor by furnace annealing.

22. A method of manufacturing a semiconductor device according to any one claim 20, wherein the step of leveling the surface of said semiconductor film is conducted by furnace annealing.

23. A method of manufacturing a semiconductor device according to any one of claim 19, wherein the step of leveling the surface of said semiconductor film is conducted between 900 and 1200° C.

24. A method of manufacturing a semiconductor device according to any one of claim 20, wherein the step of leveling the surface of said semiconductor film is conducted between 900 and 1200° C.

25. A method of manufacturing a semiconductor device according to any one of claim 19, wherein said atmosphere in said leveling step contains an inert gas.

26. A method of manufacturing a semiconductor device according to any one of claim 20, wherein said atmosphere in said leveling step contains an inert gas.

27. A method of manufacturing a semiconductor device according to any one of claim 19, wherein said atmosphere in said leveling step contains a reducing atmosphere.

28. A method of manufacturing a semiconductor device according to any one of claim 20, wherein said atmosphere in said leveling step contains a reducing atmosphere.

29. A method of manufacturing a semiconductor device according to any one of claim 19, further comprising a step of treating a surface of the semiconductor film with a buffered hydrofluoric acid before the irradiation of the laser light.

30. A method of manufacturing a semiconductor device according to any one of claim 20, further comprising a step of treating a surface of the semiconductor film with a buffered hydrofluoric acid before the irradiation of the laser light.

31. A method of manufacturing a semiconductor device according to any one of claim 19, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a mobile computer, a player using a recording medium, a goggle-type display, a digital camera, and a projector.

32. A method of manufacturing a semiconductor device according to any one of claim 20, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a mobile computer, a player using a recording medium, a goggle-type display, a digital camera, and a projector.

33. A method of manufacturing a semiconductor device according to claim 1, wherein said semiconductor device is an organic electroluminescence display device.

34. A method of manufacturing a semiconductor device according to claim 2, wherein said semiconductor device is an organic electroluminescence display device.

35. A method of manufacturing a semiconductor device according to claim 3, wherein said semiconductor device is an organic electroluminescence display device.

36. A method of manufacturing a semiconductor device according to claim 4, wherein said semiconductor device is an organic electroluminescence display device.

37. A method of manufacturing a semiconductor device according to claim 5, wherein said semiconductor device is an organic electroluminescence display device.

38. A method of manufacturing a semiconductor device according to claim 6, wherein said semiconductor device is an organic electroluminescence display device.

39. A method of manufacturing a semiconductor device according to claim 7, wherein said semiconductor device is an organic electroluminescence display device.

40. A method of manufacturing a semiconductor device according to claim 8, wherein said semiconductor device is an organic electroluminescence display device.

41. A method of manufacturing a semiconductor device according to claim 9, wherein said semiconductor device is an organic electroluminescence display device.

42. A method of manufacturing a semiconductor device according to claim 10, wherein said semiconductor device is an organic electroluminescence display device.

43. A method of manufacturing a semiconductor device according to claim 11, wherein said semiconductor device is an organic electroluminescence display device.

44. A method of manufacturing a semiconductor device according to claim 12, wherein said semiconductor device is an organic electroluminescence display device.

Pending Claims (1-46)  
U.S. Patent Application  
Serial No. 09/894,125  
Docket No.: 0756-2330  
As of July 14, 2002

45. A method of manufacturing a semiconductor device according to claim 19, wherein said semiconductor device is an organic electroluminescence display device.

46. A method of manufacturing a semiconductor device according to claim 20, wherein said semiconductor device is an organic electroluminescence display device.



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Substitution for form 1449A-PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>		Complete if Known Application Number: 09,894,125 Filing Date: June 29, 2001 First Named Inventor: Shunpei YAMAZAKI et al. Group Art Unit: 2823 Examiner Name: B. Kebede Attorney Docket Number: 0756-2330	
Sheet	1	of	1

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Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T <sup>2</sup>

Examiner Signature	<i>Brown Kebede</i>	Date Considered	<i>April 20, 2002</i>
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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete if Known

Application Number  
Filing Date June 29, 2001  
First Named Inventor Shunpei YAMAZAKI et al.  
Group Art Unit 2823  
Examiner Name B. Kebede  
Attorney Docket Number 740756-2330

Sheet

1

of

2

## U.S. PATENT DOCUMENTS

Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Office <sup>3</sup>	Number <sup>4</sup> Kind Code <sup>2</sup> (if known)				

## OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

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Examiner Signature

Brook Kebede

Date Considered

April 20, 2002

## INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Shunpei YAMAZAKI et al.

Filing Date: June 29, 2001

Group Art Unit: 2823

11017 U.S. PTO  
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